Vishay Semiconductors

# Insulated Ultrafast Rectifier Module, 120 A



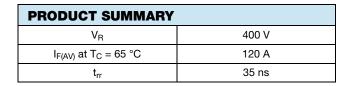
- Two fully independent diodes
- Ceramic fully insulated package (V<sub>ISOL</sub> = 2500 V<sub>AC</sub>)
- Ultrafast reverse recovery
- Ultrasoft reverse recovery current shape
- Low forward voltage
- Optimized for power conversion: welding and industrial SMPS applications
- Industry standard outline
- Plug-in compatible with other SOT-227 packages
- Easy to assemble
- Direct mounting to heatsink
- UL approved file E78996
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level

#### DESCRIPTION

The UFB120FA40P insulated modules integrate two state of the art ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The planar structure of the diodes, and the platinum doping life time control, provide a ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, dc-to-dc converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V <sub>R</sub>		400	V	
Continuous forward current per diode	١ <sub>F</sub>	$T_{\rm C} = 65 \ ^{\circ}{\rm C}$	60	А	
Single pulse forward current per diode	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	800		
Maximum power dissipation per module	PD	$T_{\rm C} = 90 \ ^{\circ}{\rm C}$	96	W	
RMS isolation voltage	VISOL	Any terminal to case, t = 1 minute	2500	V	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to 150 °C	°C	









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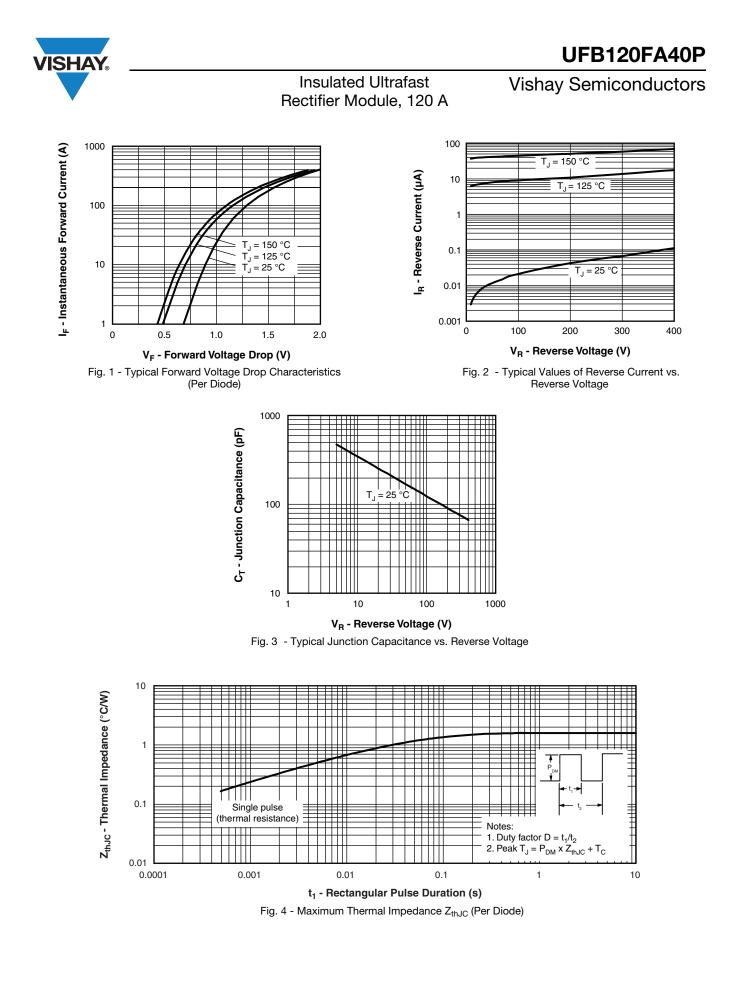
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<b>ELECTRICAL SPECIFICATIONS PER DIODE</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA	400	-	-	
Forward voltage	M	I <sub>F</sub> = 60 A	-	1.16	1.37	V mA
	V <sub>FM</sub>	$I_F = 60 \text{ A}, T_J = 150 \text{ °C}$	-	0.96	1.13	
Reverse leakage current	I <sub>RM</sub> -	$V_R = V_R$ rated	-	-	0.1	mA
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	1	
Junction capacitance	CT	V <sub>R</sub> = 400 V	-	67	-	pF

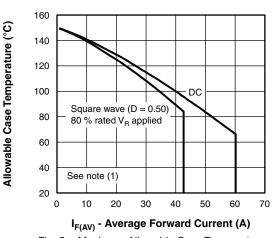
<b>DYNAMIC RECOVERY CHARACTERISTICS PER DIODE</b> ( $T_J$ = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F$ = 1.0 A, $dI_F/dt$ = 200 A/µs, $V_R$ = 30 V		-	30	35	
Reverse recovery time t <sub>rr</sub>	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	65	-	ns
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 50 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	128	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	7.4	-	A
		T <sub>J</sub> = 125 °C		-	17.8	-	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	240	-	nC
		T <sub>J</sub> = 125 °C		-	1139	-	

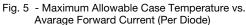
THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single diode conducting	Р		-	0.99	1.24	
Junction to case, both diodes conducting	– R <sub>thJC</sub>		-	0.49	0.62	°C/W
Case to heatsink	R <sub>thCS</sub>	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque			-	1.3	-	Nm

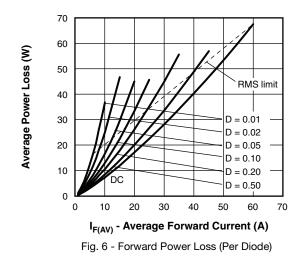


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#### Note

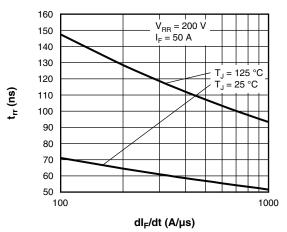


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

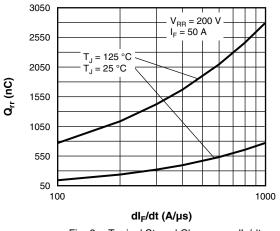


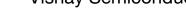
Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



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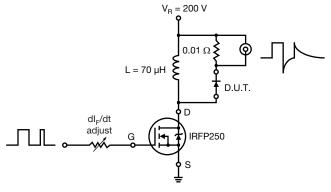
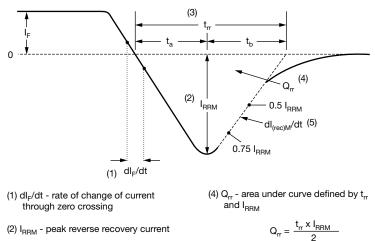


Fig. 9 - Reverse Recovery Parameter Test Circuit



 (3) t<sub>rr</sub> - reverse recovery time measured from zero crossing point of negative

going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.

(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

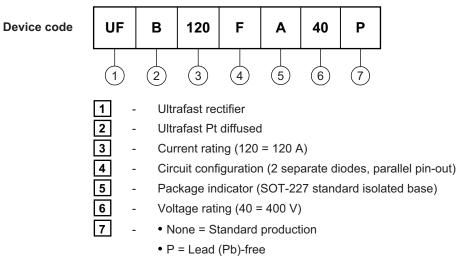
Fig. 10 - Reverse Recovery Waveform and Definitions



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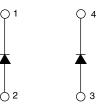
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#### **ORDERING INFORMATION TABLE**



Quantity per tube is 10, M4 screw and washer included

#### **CIRCUIT CONFIGURATION**



LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95036				
Packaging information	www.vishay.com/doc?95037				

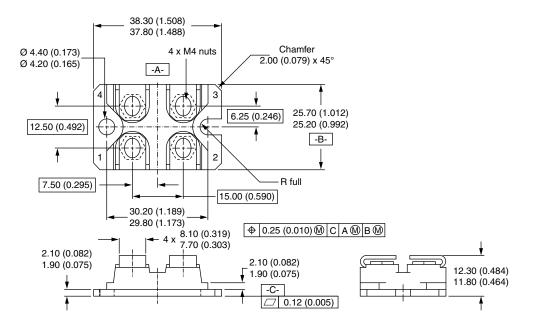


## **Outline Dimensions**

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SOT-227

#### **DIMENSIONS** in millimeters (inches)



#### Notes

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- Controlling dimension: millimeter



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